

# SILICON POWER TRANSISTOR 2SA1744

## PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

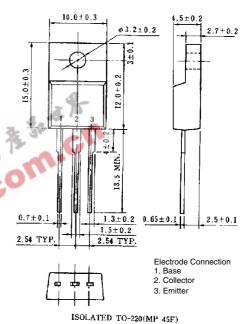
The 2SA1744 is a power transistor developed for high-speed switching and features a high hee at Low VCE(sat). This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

#### **FEATURES**

- High hee and low Vce(sat): hfe  $\geq 100 \text{ (Vce} = -2 \text{ V, Ic} = -3 \text{ A)}$  $V_{CE(sat)} \le 0.3 \text{ V (Ic} = -8 \text{ A, IB} = -0.4 \text{ A)}$
- Full-mold package that does not require an insulating board or bushing

# PACKAGE DRAWING (UNIT: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-100	٧
Collector to emitter voltage	VCEO	-60	٧
Emitter to base voltage	V <sub>EBO</sub>	-7.0	٧
Collector current (DC)	Ic(DC)	-15	Α
Collector current (pulse)	IC(pulse)*	-30	Α
Base current (DC)	I <sub>B(DC)</sub>	-7.5	Α
Total power dissipation	P⊤ (Tc = 25°C)	30	W
Total power dissipation	P⊤ (Ta = 25°C)	2.0	W
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

<sup>\*</sup> PW  $\leq$  300  $\mu$ s, duty cycle  $\leq$  10%

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



#### ELECTRICAL CHARACTERISTICS (TA = 25°C)

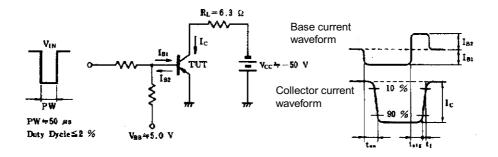
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	$I_{C} = -8.0 \text{ A}, I_{B} = -0.8 \text{ A}, L = 1 \text{ mH}$	-60			٧
Collector to emitter voltage	VCEX(SUS)	$I_{C} = -8.0 \text{ A}, \ I_{B1} = -I_{B2} = -0.8 \text{ A},$ $V_{BE(OFF)} = 1.5 \text{ V}, \ L = 180 \ \mu\text{H}, \ clamped$	-60			V
Collector cutoff current	Ісво	$V_{CB} = -60 \text{ V}, I_E = 0$			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -60 \text{ V}, \text{ Rbe} = 50 \ \Omega, \text{ Ta} = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V}$			-10	μΑ
Collector cutoff current	ICEX2	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V},$ $T_A = 125^{\circ}C$			-1.0	mA
Emitter cutoff current	ІЕВО	V <sub>EB</sub> = -5.0 V, I <sub>C</sub> = 0			-10	μΑ
DC current gain	h <sub>FE1</sub> *	Vce = -2.0 V, Ic = -1.5 A	100			
DC current gain	h <sub>FE2</sub> *	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -3.0 \text{ A}$	100		400	
DC current gain	h <sub>FE3</sub> *	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -8.0 \text{ A}$	60			
Collector saturation voltage	V <sub>CE(sat)1</sub> *	$I_{C} = -8.0 \text{ A}, I_{B} = -0.4 \text{ A}$	4	99-	-0.3	٧
Collector saturation voltage	V <sub>CE(sat)2</sub> *	Ic = -12 A, I <sub>B</sub> = -0.6 A	a st m		-0.5	V
Base saturation voltage	V <sub>BE(sat)1</sub> *	$I_{C} = -8.0 \text{ A}, I_{B} = -0.4 \text{ A}$	C		-1.2	V
Base saturation voltage	V <sub>BE(sat)2</sub> *	Ic = -12 A, Iв = -0.6 A	4		-1.5	V
Collector capacitance	Cob	Vcв = −10 V, I∈ = 0, f = 1.0 MHz		300		pF
Gain bandwidth product	fτ	$V_{CE} = -10 \text{ V, Ic} = -1.5 \text{ A}$		80		MHz
Turn-on time	ton	$lo = -8.0 \text{ A}, R_L = 6.3 \Omega,$			0.3	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.4 \text{ A}, \text{ Vcc} \cong -50 \text{ V}$ Refer to the test circuit.			1.5	μs
Fall time	tr	Tiele to the test circuit.			0.3	μs

<sup>\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

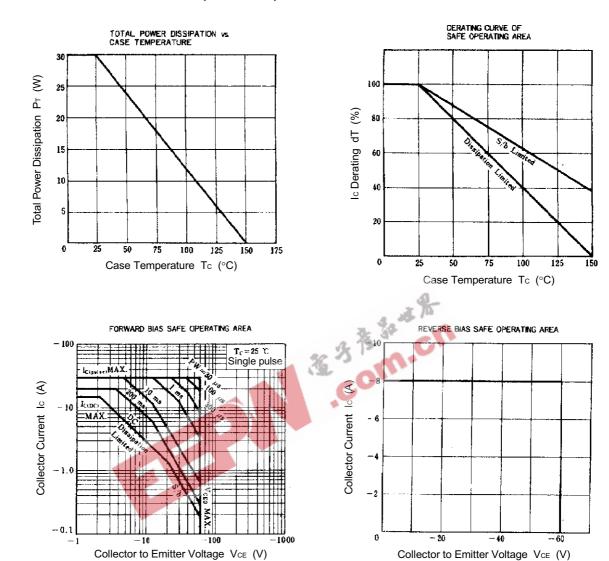
#### **hfe CLASSIFICATION**

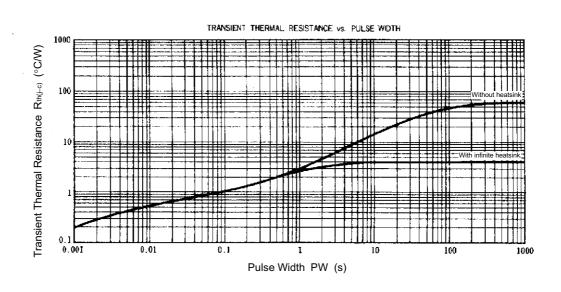
Marking	M	L	К
h <sub>FE2</sub>	100 to 200	150 to 300	200 to 400

## SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

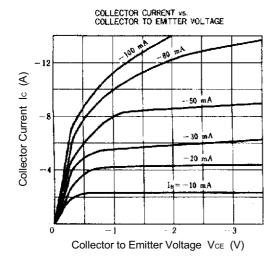


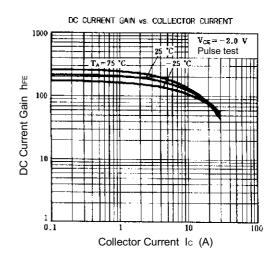
#### TYPICAL CHARACTERISTICS (TA = 25°C)

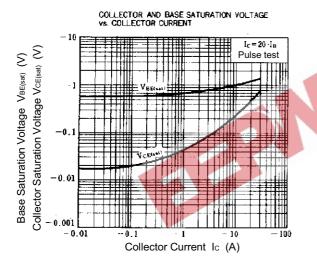


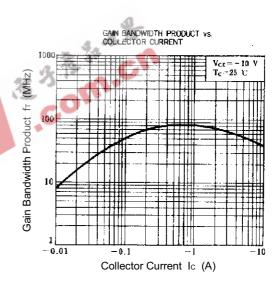


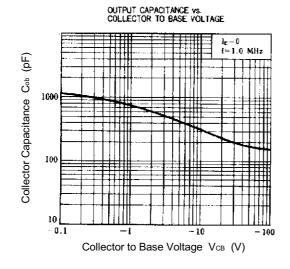
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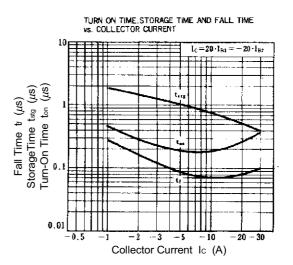












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